

Title (en)
Mems sensor and mems sensor manufacture method

Title (de)
MEMS-Sensor und MEMS-Sensorherstellungsverfahren

Title (fr)
Capteur MEMS et procédé de fabrication de capteur MEMS

Publication
EP 2202526 A3 20120222 (EN)

Application
EP 09015875 A 20091222

Priority
JP 2008334018 A 20081226

Abstract (en)
[origin: EP2202526A2] Trench separating mass body and support is defined in support substrate, and flexible beam cross is defined in semiconductor layer, in SOI. The semiconductor layer and intermediate insulator of the SOI are etched in crossed region of the flexible beam cross and in a looped region above the support body. Connector layer is buried in the etched recesses. The semiconductor layer is patterned into the flexible beam cross above the mass body. The trench is etched in the support substrate exposing the intermediate insulator, which is then etched to form a gap between the mass body and flexible beam cross. The connector layer in the crossed region couples the mass body and flexible beam cross, and the connector layer outside the flexible beam cross couples the flexible beam cross and support body. Stopper is formed by extending the connector layer, or leaving the semiconductor layer, above the mass body corners.

IPC 8 full level
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CPC (source: EP US)
G01P 15/0802 (2013.01 - EP US); **G01P 15/123** (2013.01 - EP US); **G01P 15/18** (2013.01 - EP US); **G01P 2015/084** (2013.01 - EP US)

Citation (search report)
• [A] US 2007214888 A1 20070920 - NOMURA AKIHIKO [JP]
• [A] US 2006094148 A1 20060504 - NAKAMIZO YOSHIYUKI [JP], et al
• [AD] JP 2006064532 A 20060309 - MATSUSHITA ELECTRIC WORKS LTD

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

Designated extension state (EPC)
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